

MC74VHCT14A

Hex Schmitt Inverter

The MC74VHCT14A is an advanced high speed CMOS Schmitt inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

Pin configuration and function are the same as the MC74VHCT04A, but the inputs have hysteresis and, with its Schmitt trigger function, the VHCT14A can be used as a line receiver which will receive slow input signals.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT14A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 5.5$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 2.0 \mu A$ (Max) at $T_A = 25^\circ C$
- TTL-Compatible Inputs: $V_{IL} = 0.8$ V; $V_{IH} = 2.0$ V
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: 60 FETs or 15 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



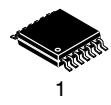
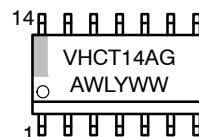
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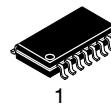
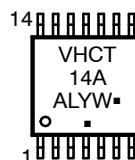
MARKING DIAGRAMS



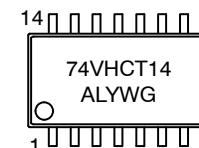
SOIC-14
D SUFFIX
CASE 751A



TSSOP-14
DT SUFFIX
CASE 948G



SOEIAJ-14
M SUFFIX
CASE 965



A = Assembly Location

WL, L = Wafer Lot

Y, YY = Year

WW, W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs	Outputs
A	Y
L H	H L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74VHCT14A

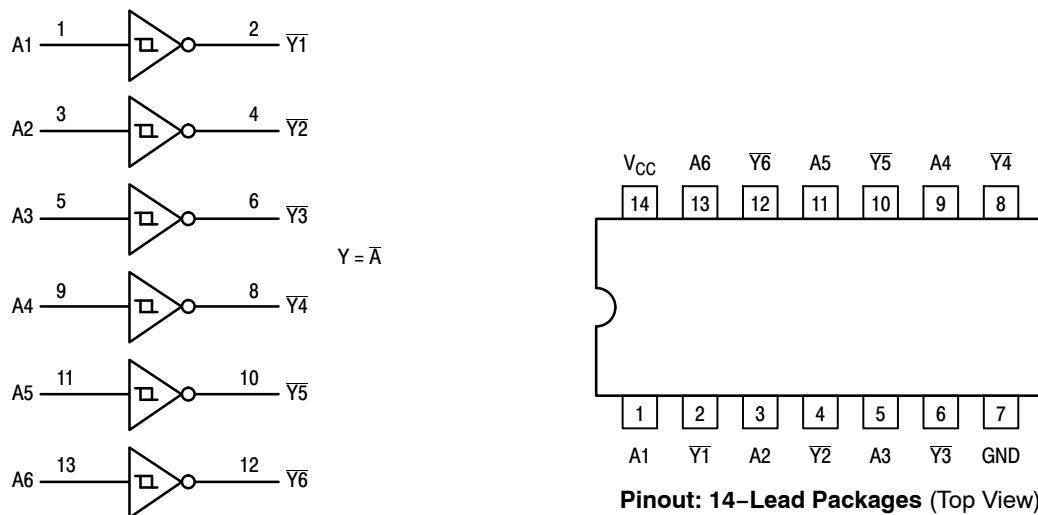


Figure 1. Logic Diagram

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
DC Supply Voltage	V_{CC}	-0.5 to +7.0	V
DC Input Voltage	V_{IN}	-0.5 to +7.0	V
DC Output Voltage Output in HIGH or LOW State (Note 1)	V_{OUT}	-0.5 to $V_{CC} + 0.5$ V	V
$V_{CC} = 0$ V	V_{OUT}	-0.5 to 7.0	V
DC Input Diode Current	I_{IK}	-20	mA
DC Output Diode Current	I_{OK}	± 20	mA
DC Output Source/Sink Current	I_O	± 25	mA
DC Supply Current per Supply Pin	I_{CC}	± 50	mA
DC Ground Current per Ground Pin	I_{GND}	± 50	mA
Storage Temperature Range	T_{STG}	-65 to +150	°C
Lead Temperature, 1 mm from Case for 10 Seconds	T_L	260	°C
Junction Temperature under Bias	T_J	+150	°C
Thermal Resistance SOIC TSSOP	θ_{JA}	125 170	°C/W
Power Dissipation in Still Air SOIC TSSOP	P_D	500 450	mW
ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V_{ESD}	>2000 >200 2000	V
Latchup Performance Above V_{CC} and Below GND at 85°C (Note 5)	$I_{Latchup}$	± 300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

MC74VHCT14A

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min			Max			Unit
Supply Voltage	V _{CC}	4.5			5.5			V
Input Voltage	V _I	0			5.5			V
Output Voltage (Note 6)	V _O	0			V _{CC}			V
V _{CC} = 0 V	V _O	0			5.5			V
Operating Free-Air Temperature	T _A	-55			+125			°C

6. I_O absolute maximum rating must be observed.

DC ELECTRICAL CHARACTERISTICS

Parameter	Test Conditions	Symbol	V _{CC} V	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
Positive Threshold Voltage		V _{T+}	4.5 5.5			1.9 2.1			1.9 2.1		V
Negative Threshold Voltage		V _{T-}	4.5 5.5	0.5 0.6			0.5 0.6		0.5 0.6		V
Hysteresis Voltage		V _H	4.5 5.5	0.40 0.40		1.40 1.50	0.40 0.40	1.40 1.50	0.40 0.40	1.40 1.50	V
Minimum High-Level Output Voltage I _{OH} = -50 μA	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	V _{OH}	4.5	4.4	4.5		4.4		4.4		V
	I _{OH} = -8.0 mA		5.5	3.94			3.80		3.66		
Maximum Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	V _{OL}	4.5		0.0	0.1		0.1		0.1	V
	I _{OL} = 8.0 mA		5.5			0.36		0.44		0.52	
Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	I _{IN}	0 to 5.5			±0.1		±1.0		±1.0	μA
Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	I _{CC}	5.5			2.0		20		40	μA
Quiescent Supply Current	Input: V _{IN} = 3.4 V	I _{CCT}	5.5			1.35		1.50		1.65	mA
Output Leakage Current	V _{OUT} = 5.5 V	I _{OFF}	0.0			0.5		5.0		10	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Parameter	Test Conditions	Symbol	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
Maximum Propagation Delay, A to \bar{Y}	V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF	t _{PLH} , t _{PHL}		5.5 7.0	7.6 9.6	1.0 1.0	9.0 11.0	1.0 1.0	11.5 13.5	ns
Maximum Input Capacitance		C _{IN}		2.0	10		10		10	pF
Power Dissipation Capacitance (Note 7)		C _{PD}	Typical @ 25°C, V _{CC} = 5.0 V							pF
			11							

7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/6 (per buffer). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0 ns, C_L = 50 pF, V_{CC} = 5.0 V)

Characteristic	Symbol	T _A = 25°C			Unit
		Typ		Max	
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	0.8		1.0	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	-0.8		-1.0	V
Minimum High Level Dynamic Input Voltage	V _{IHD}			2.0	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}			0.8	V

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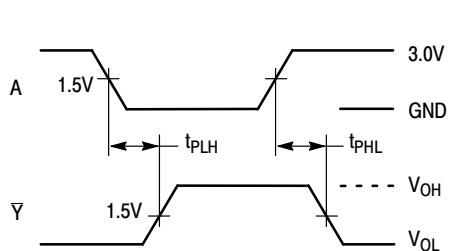
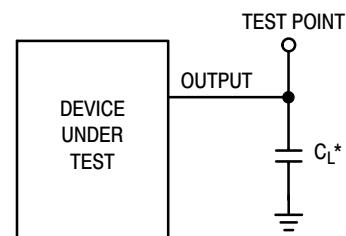


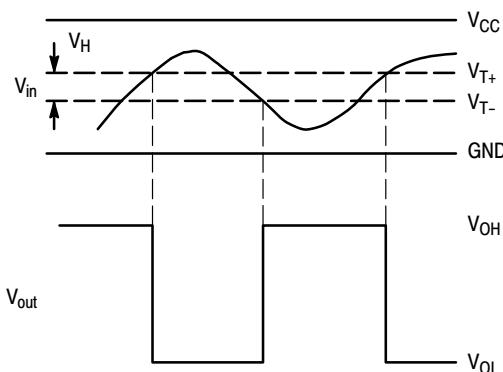
Figure 2. Switching Waveforms



*Includes all probe and jig capacitance

Figure 3. Test Circuit

(a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times



(b) A Schmitt-Trigger Offers Maximum Noise Immunity

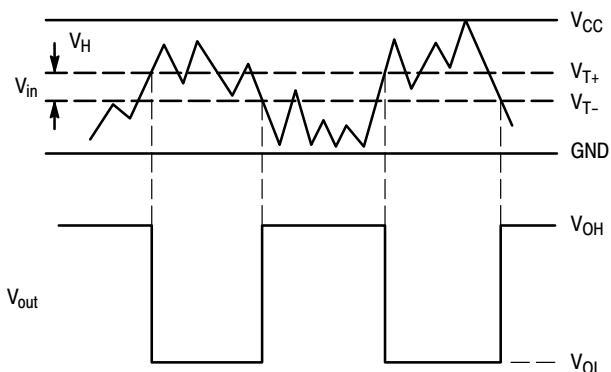


Figure 4. Typical Schmitt-Trigger Applications

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT14ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT14ADTR2G	TSSOP-14*	
MC74VHCT14AMG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74VHCT14AMELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

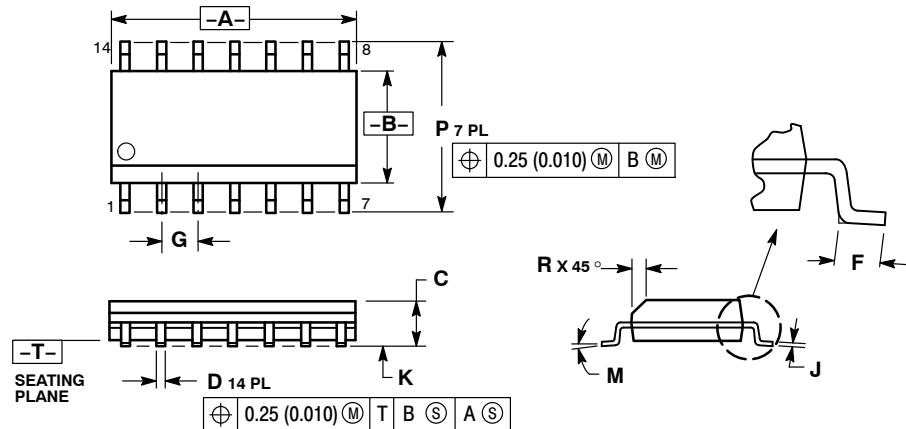
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*These packages are inherently Pb-Free.

MC74VHCT14A

PACKAGE DIMENSIONS

**SOIC-14
D SUFFIX
CASE 751A-03
ISSUE J**

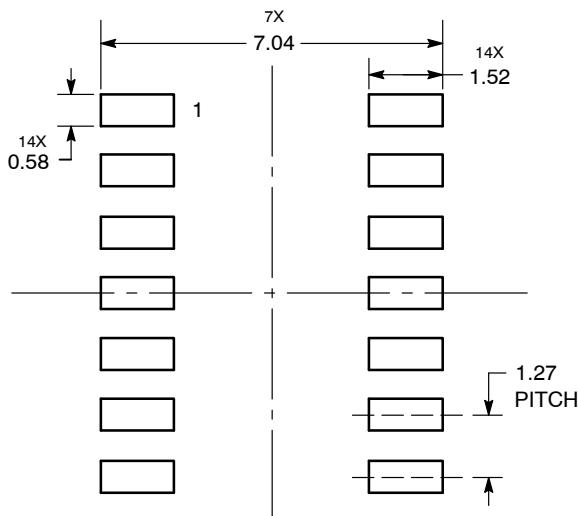


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

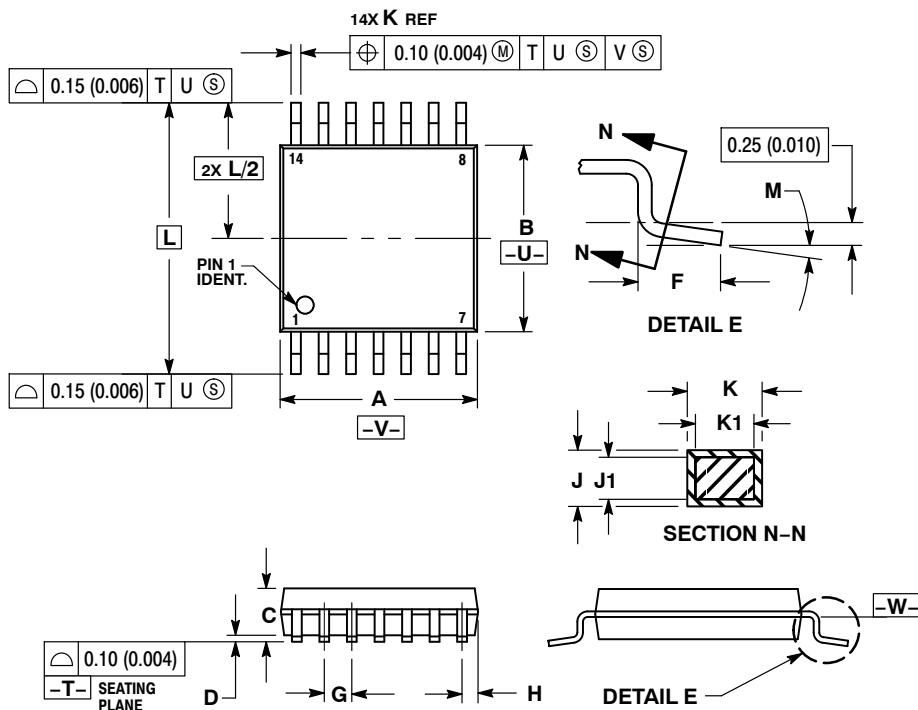
SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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TSSOP-14
CASE 948G-01
ISSUE B



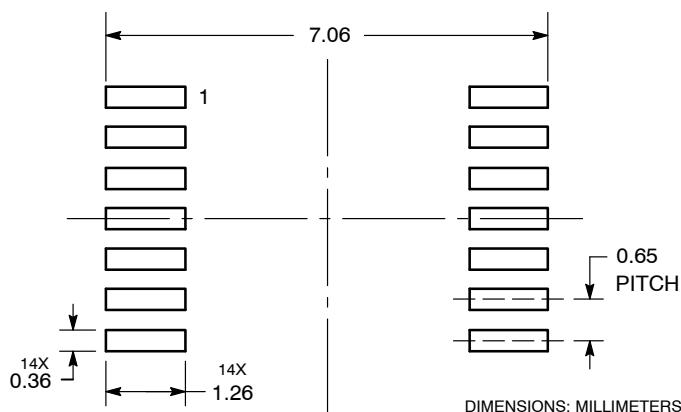
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W .

MILLIMETERS INCHES

DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

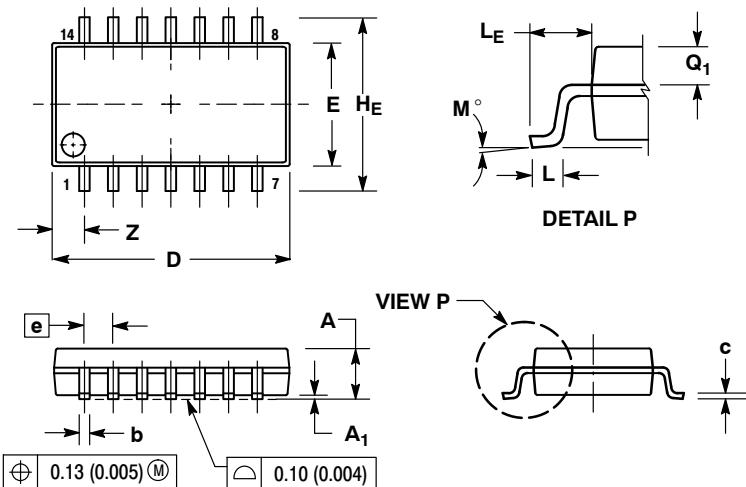
SOLDERING FOOTPRINT



MC74VHCT14A

PACKAGE DIMENSIONS

SOEIAJ-14
CASE 965-01
ISSUE B



NOTES:

- Dimensioning and tolerancing per ANSI Y14.5M, 1982.
- Controlling dimension: millimeter.
- Dimensions D and E do not include mold flash or protrusions and are measured at the parting line. Mold flash or protrusions shall not exceed 0.15 (0.006) per side.
- Terminal numbers are shown for reference only.
- The lead width dimension (b) does not include dambar protrusion. Allowable dambar protrusion shall be 0.08 (0.003) total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the foot. Minimum space between protrusions and adjacent lead to be 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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